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Mullish

Information for IDS

1c879 U.S. PTO  
10/082205  
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I. Prior application:

(i) United States Patent Application

No

(ii) Others

No

II. Prior Art:

(i) articles

1. \* H. Miwa et al.; "A 140mm<sup>2</sup> 64Mb AND Flash Memory with A 0.4μm Technology"
- \* IEEE International Solid-State Circuit Conference 1996, p34-35, (1996)
- \* cited in the specification at page 1
2. \* T. Jung et al.; "A 3.3V 128Mb Multi-Level NAND Flash Memory for Mass Storage Applications"
- \* IEEE International Solid-State Circuit Conference 1996, p32-33, (1996)
- \* cited in the specification at page 2

(ii) U. S. P.

No

(iii) Japanese Patent Application

No

(iv) European Patent Application

No

(v) International Patent Application

No

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